廖洺漢
著作目錄

期刊論文

1. M.-H. Liao*, C.-P. Hsieh, and C.-C. Lee* (2017, Jul). The investigation of self-heating effect on Si1-xGex FinFETs with different device structures, Ge concentration, and operated voltages. *AIP Advances*, Vol. 7, p. 055105. 本人為第一作者、通訊作者.
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